Preferred Device

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Four Modes
- **%** Indicates UL Registered File #E69369
- Device Marking: Logo, Device Type, e.g., MAC15A6FP, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage ⁽¹⁾ (T _J = -40 to +125°C, Sine Wave 50 to 60 Hz, Gate Open) MAC15A6FP MAC15A8FP MAC15A10FP	V _{DRM} , V _{RRM}	400 600 800	Volts
On-State RMS Current $(T_C = +80^{\circ}C)^{(2)}$ Full Cycle Sine Wave 50 to 60 Hz $(T_C = +95^{\circ}C)$	I _{T(RMS)}	15 12	Amps
Peak Nonrepetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _C = +80°C) Preceded and followed by rated current	I _{TSM}	150	Amps
Circuit Fusing (t = 8.3 ms)	l ² t	93	A ² s
Peak Gate Power (T _C = +80°C, Pulse Width = 2.0 μs)	P _{GM}	20	Watts
Average Gate Power (T _C = +80°C, t = 8.3 ms)	P _{G(AV)}	0.5	Watt
Peak Gate Current (Pulse Width $\leq 1.0 \mu sec; T_C = 80^{\circ}C$)	I _{GM}	2.0	Amps
Peak Gate Voltage (Pulse Width ≤ 1.0 μsec; T _C = 80°C)	V _{GM}	10	Volts
RMS Isolation Voltage (T _A = 25°C, Relative Humidity ≤ 20%) (%)	V _(ISO)	1500	Volts
Operating Junction Temperature	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

- (1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- (2) The case temperature reference point for all $T_{\rm C}$ measurements is a point on the center lead of the package as close as possible to the plastic body.



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ISOLATED TRIAC (9\) 15 AMPERES RMS 400 thru 800 VOLTS





ISOLATED TO-220 Full Pack CASE 221C STYLE 3

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		

ORDERING INFORMATION

Device	Package	Shipping
MAC15A6FP	ISOLATED TO220FP	500/Box
MAC15A8FP	ISOLATED TO220FP	500/Box
MAC15A10FP	ISOLATED TO220FP	500/Box

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	2.0	°C/W
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T _L	260	°C

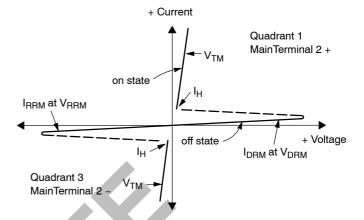
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•		•	•
$ \begin{array}{ll} \mbox{Peak Repetitive Blocking Current} & T_{J} = 25^{\circ}\mbox{C} \\ \mbox{(V_{D} = Rated V_{DRM}, V_{RRM}; Gate Open)} & T_{J} = 125^{\circ}\mbox{C} \\ \end{array} $	I _{DRM} , I _{RRM}		_	10 2.0	μA mA
ON CHARACTERISTICS					
Peak On-State Voltage ⁽¹⁾ (I _{TM} = ±21 A Peak	V _{TM}	_	1.3	1.6	Volts
Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, R_L = 100 Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	l _{GT}	- - -		50 50 50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, R _L = 100 Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	Ver	OPN	0.9 0.9 1.1 1.4	2.0 2.0 2.0 2.5	Volts
Gate Non-Trigger Voltage (Main Terminal Voltage = Rated V_{DRM} , R_L = 100 Ω , T_J = +110°C) All 4 Quadrants	V _{GD}	0.2	_	_	Volts
Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = ±200 mA)	lμ	_	6.0	40	mA
Turn-On Time $(V_D = Rated\ V_{DRM},\ I_{TM} = 17\ A,\ I_{GT} = 120\ mA,$ Rise Time = 0.1 μ s, Pulse Width = 2 μ s)	t _{gt}	_	1.5	_	μS
DYNAMIC CHARACTERISTICS					
Critical Rate of Rise of Commutation Voltage $(V_D = Rated\ V_{DRM},\ V_{RRM},\ I_{TM} = 21\ A,\ Commutating\ di/dt = 7.6\ A/ms,\ Gate\ Unenergized,\ T_C = 80^{\circ}C)$	dv/dt(c)	_	5.0	_	V/μs

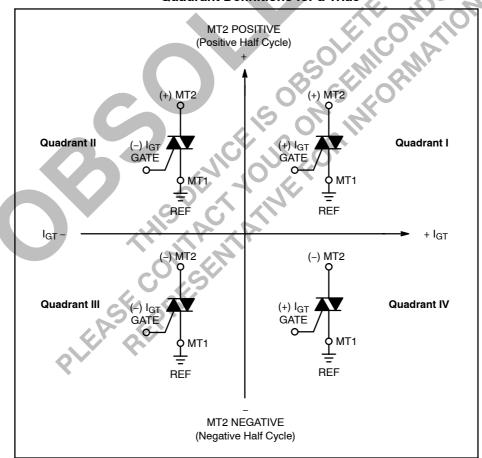
⁽¹⁾ Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

TYPICAL CHARACTERISTICS

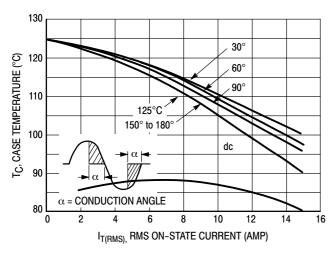
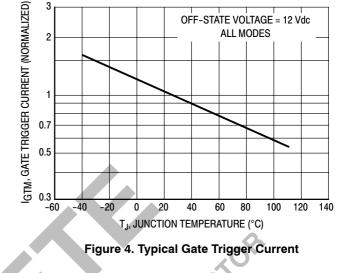


Figure 1. RMS Current Derating



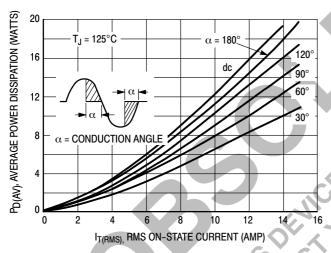


Figure 2. On-State Power Dissipation

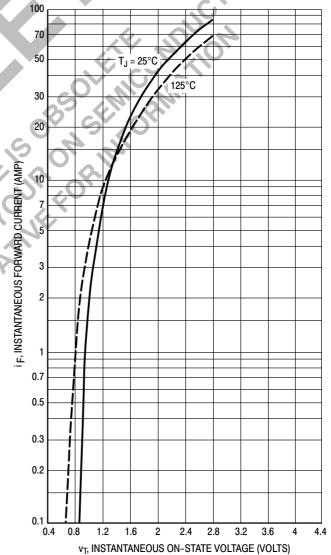


Figure 3. Typical Gate Trigger Voltage

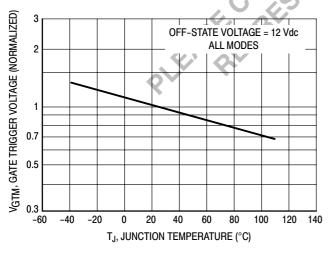
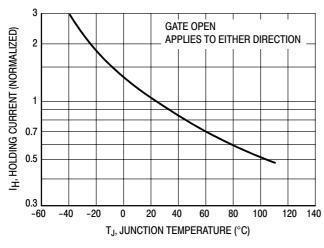


Figure 5. Maximum On-State Characteristics



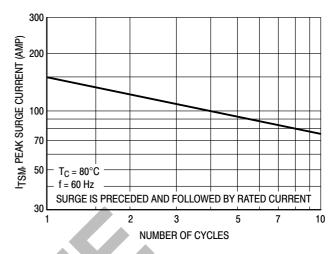
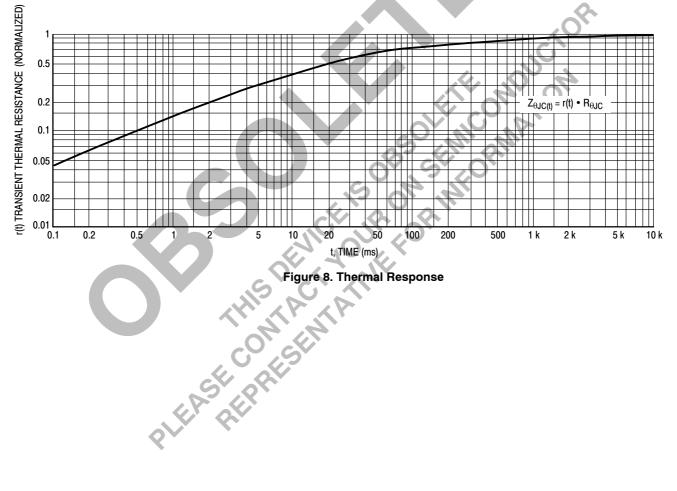


Figure 6. Typical Holding Current

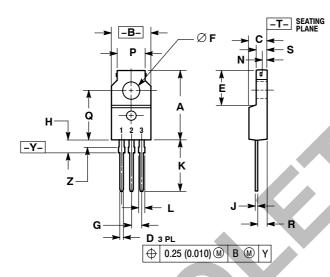
Figure 7. Maximum Nonrepetitive Surge Current



PACKAGE DIMENSIONS

ISOLATED TO-220 Full Pack

CASE 221C-02 **ISSUE C**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.680	0.700	17.28	17.78
В	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
H	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049		1.25	
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

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